

## F G.2

Z BLK	<u>}</u>	BLK OAT	AREA) 30	/ BLK		<u> </u>	(SUBETITUTION AREA)31		/ BLK	
ECC FOR "MO "		ECC FOR		ECC FOR "Mn "			ECC FOR			
3 "S0" MANAGEMENT INFORMATION "M0" IN SECTOR ADDRESS "0"		3 "St"   MANAGEMENT INFORMATION "MK"   IN SECTOR ADDRESS "K"	DEFECT SECTOR	3 "Sn"   MANAGEMENT INFORMATION "Mn"   IN SECTOR ADDRESS "n"			SK   MANAGEMENT INFORMATION "MX"   IN SECTOR ADDRESS "X"			MANAGEMENT TABLE
ECC FOR "SO"		ECC FOR "St	門	ECC FOR "Sn"			ECC FOR "SK"			ION AREA
SECTOR DATA "S0" OF 512 BYTES	::	SECTOR DATA "SK" OF 512 BYTES		SECTOR DATA "Sn" OF 512 BYTES		•	SECTOR DATA "SK" OF 512 BYTES		PARAMETER SECTOR	SUBETITUT
SECTOR ADDRESS	· ·	SECTOR ADDRESS	<u></u>	SECTOR ADDRESS	=		SECTOR ADDRESS	<	32	

FIG.3

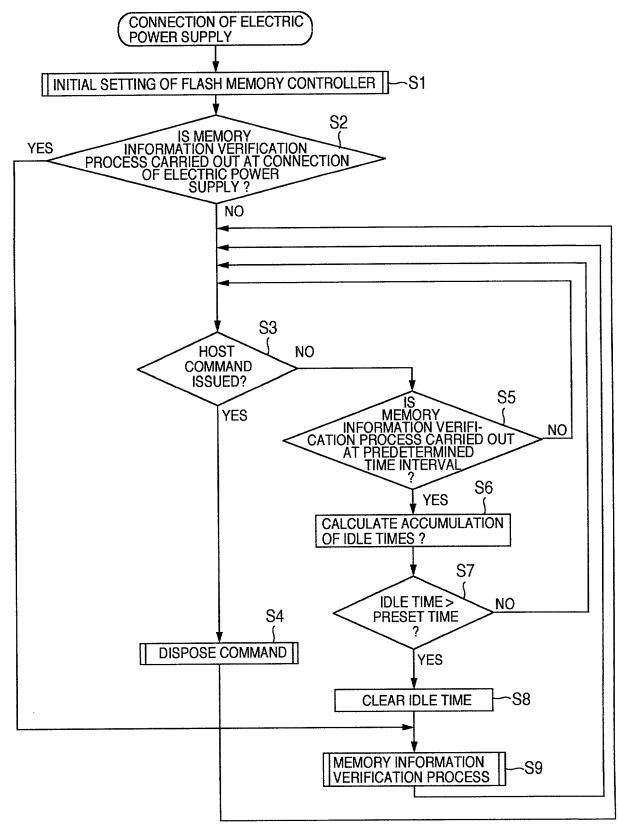


FIG.4

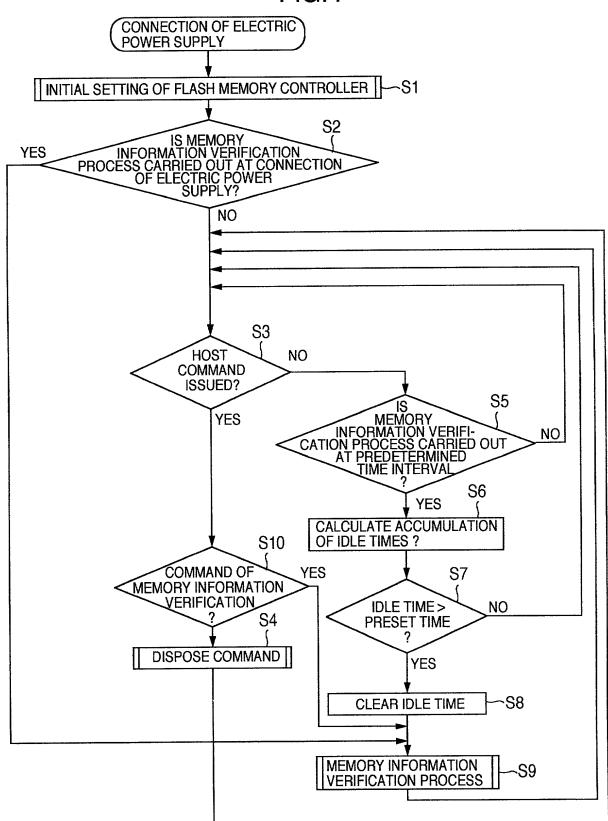
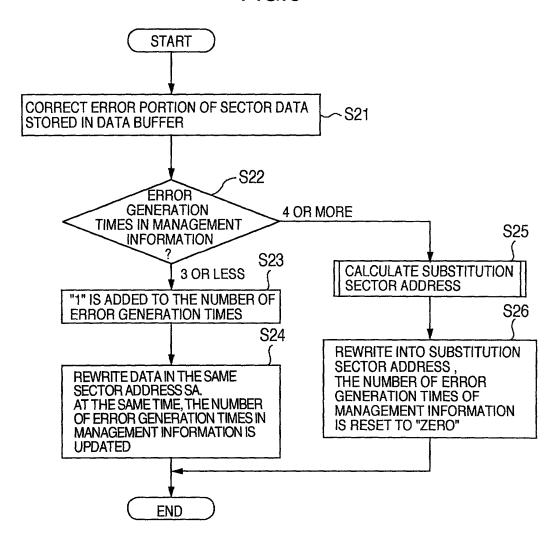


FIG.5 **START** INITIALIZE SECTOR ADDRESS OF FLASH MEMORY ~S11 **S12** READ ONE SECTOR DATA FROM SA INTO DATA BUFFE AT THE SAME TIME, DETECT ERROR IN SECTOR DATA BY ECC CIRCUIT S13 YES **ERROR S14** EXISTS ? PROCESS FOR ERROR CORRECTION NO **S15** PROCESS FOR **REWRITTING DATA S16** YES SA=MAXIMUM VALUE? **END** NO SA=SA+1 **S17** S18 YES IS HOST COMMAND ISSUED? S19 NO MEMORY YES **INFORMATION VERIFICATION** COMMAND S20 ¥ NO DISPOSE OTHER COMMANDS

FIG.6



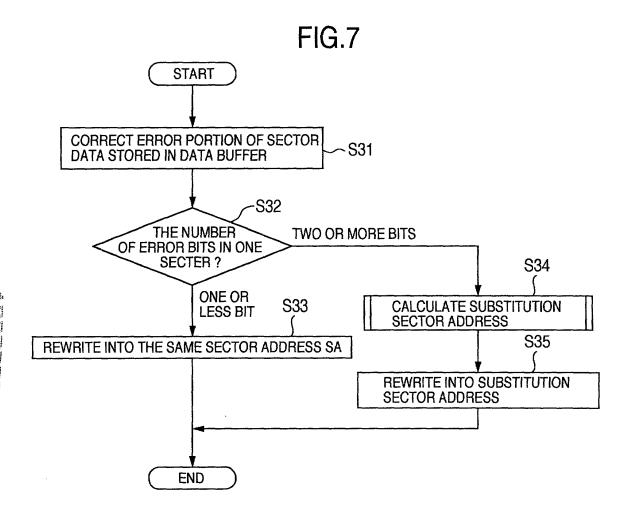


FIG.8

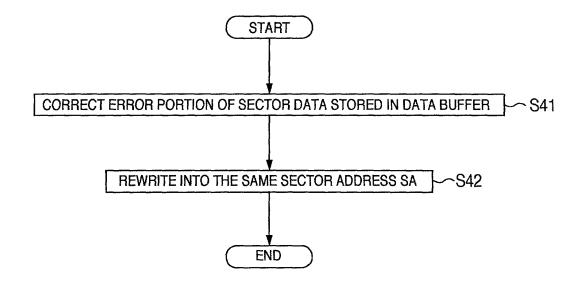
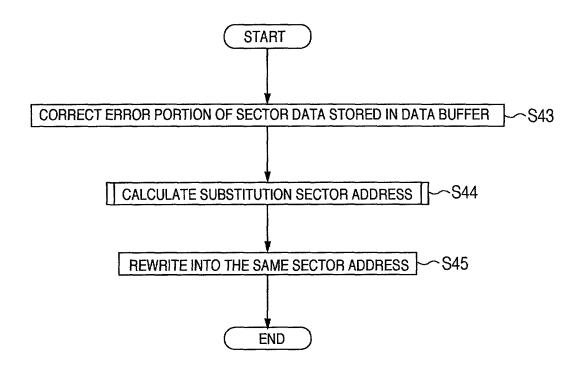


FIG.9



**FIG.10** 

